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Team Nexperia



BC846BS 65 V, 100 mA NPN/NPN general-purpose transistor Rev. 01 — 24 August 2009 Produ

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package I		PNP/PNP	NPN/PNP	
	NXP	JEITA	complement	complement	
BC846BS	SOT363	SC-88	BC856BS	BC846BPN	

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	65	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 2 \text{ mA}$	200	300	450	



65 V, 100 mA NPN/NPN general-purpose transistor

Pinning information 2.

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2	1 2 3	
6	collector TR1		1 2 3
			sym020

Ordering information 3.

Table 4. Ordering information						
Type number	Package					
	Name	Description	Version			
BC846BS	SC-88	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
BC846BS	*E5
[1] * = -: made in Hong Kong * = p: made in Hong Kong	

- * = t: made in Malaysia
- * = W: made in China

Limiting values 5.

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{tabular}{ c c c c } \hline Per transistor & & & & & & & & & & & & & & & & \\ \hline V_{CBO} & collector-base voltage & open emitter & - & & & & & & & & & & & & \\ \hline V_{CEO} & collector-emitter voltage & open base & - & & & & & & & & & & & & & \\ \hline V_{EBO} & emitter-base voltage & open collector & - & & & & & & & & & & & & \\ \hline V_{EBO} & emitter-base voltage & open collector & - & & & & & & & & & & & \\ \hline I_C & collector current & & & & & & & & & & & & & & & & & & &$,		
$\begin{array}{c c c c c c c } V_{CBO} & collector-base voltage & open emitter & - & 80 & V \\ V_{CEO} & collector-emitter voltage & open base & - & 65 & V \\ V_{EBO} & emitter-base voltage & open collector & - & 6 & V \\ I_C & collector current & open collector & - & 100 & mA \\ I_{CM} & peak collector current & single pulse; & - & 200 & mA \\ I_{BM} & peak base current & single pulse; & - & 200 & mA \\ I_{BM} & peak base current & single pulse; & - & 200 & mA \\ I_{D} & I_{D} & I_{D} & I_{D} & I_{D} & I_{D} & I_{D} \\ I_{D} & I_{$	Symbol	Parameter	Conditions	Min	Мах	Unit
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Per transis	stor				
$\label{eq:VEBO} \begin{array}{c} \mbox{emitter-base voltage} & \mbox{open collector} & - & 6 & V \\ I_{C} & \mbox{collector current} & - & 100 & mA \\ I_{CM} & \mbox{peak collector current} & \mbox{single pulse;} & - & 200 & mA \\ I_{BM} & \mbox{peak base current} & \mbox{single pulse;} & - & 200 & mA \\ I_{p} \leq 1 \ ms & - & 200 & mA \end{array}$	V _{CBO}	collector-base voltage	open emitter	-	80	V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{CEO}	collector-emitter voltage	open base	-	65	V
$\label{eq:loss} \begin{array}{c} I_{CM} & \text{peak collector current} & \text{single pulse}; & - & 200 & \text{mA} \\ I_{BM} & \text{peak base current} & \text{single pulse}; & - & 200 & \text{mA} \\ t_p \leq 1 \text{ ms} & & t_p \leq 1 \text{ ms} \end{array}$	V _{EBO}	emitter-base voltage	open collector	-	6	V
$t_p \le 1 \text{ ms}$ I_{BM} peak base current single pulse; - 200 mA $t_p \le 1 \text{ ms}$	l _C	collector current		-	100	mA
$t_p \le 1 \text{ ms}$	I _{CM}	peak collector current	•	-	200	mA
P_{tot} total power dissipation $T_{amb} \le 25 \ ^{\circ}C$ [1] - 200 mW	I _{BM}	peak base current		-	200	mA
	P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	200	mW

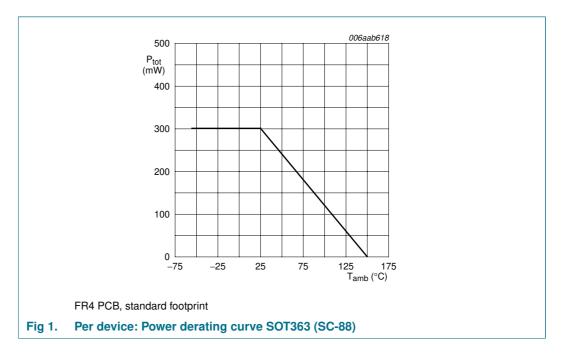
65 V, 100 mA NPN/NPN general-purpose transistor

 Table 6.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

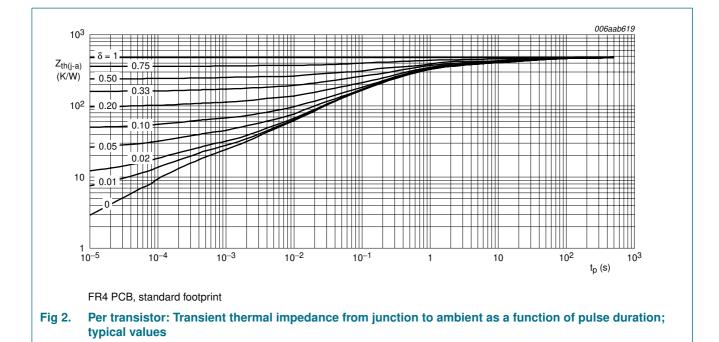
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	230	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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BC846BS

65 V, 100 mA NPN/NPN general-purpose transistor



7. Characteristics

Table 8.Characteristics

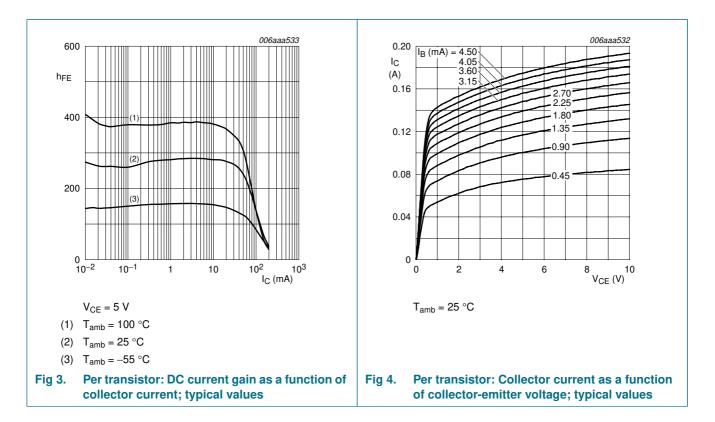
 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per trans	Per transistor						
I _{CBO}	collector-base cut-off	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA	
	current	$\label{eq:VCB} \begin{array}{l} V_{CB}=30 \text{ V}; \text{ I}_{E}=0 \text{ A}; \\ T_{j}=150 \ ^{\circ}\text{C} \end{array}$	-	-	5	μA	
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA	
h _{FE}	DC current gain	$V_{CE} = 5 V$					
		I _C = 10 μA	-	280	-		
		$I_{\rm C} = 2 \rm mA$	200	300	450		
V _{CEsat}	collector-emitter	$I_{C} = 10 \text{ mA}; I_{B} = 0.5 \text{ mA}$	-	55	100	mV	
	saturation voltage	$I_{C} = 100 \text{ mA}; I_{B} = 5 \text{ mA}$	-	200	300	mV	
V _{BEsat}	base-emitter	$I_{C} = 10 \text{ mA}; I_{B} = 0.5 \text{ mA}$	-	755	850	mV	
	saturation voltage	$I_{C} = 100 \text{ mA}; I_{B} = 5 \text{ mA}$	-	1000	-	mV	
V _{BE}	base-emitter voltage	$V_{CE} = 5 V$					
		$I_{\rm C} = 2 \rm mA$	580	650	700	mV	
		I _C = 10 mA	-	-	770	mV	

65 V, 100 mA NPN/NPN general-purpose transistor

				_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	1.9	-	pF
C _e	emitter capacitance	$\label{eq:Veb} \begin{split} V_{EB} &= 0.5 \text{ V}; \text{I}_{C} = \text{I}_{c} = 0 \text{ A}; \\ \text{f} &= 1 \text{MHz} \end{split}$	-	11	-	pF
f _T	transition frequency	$\label{eq:VCE} \begin{array}{l} V_{CE} = 5 \ V; \ I_{C} = 10 \ mA; \\ f = 100 \ MHz \end{array}$	100	-	-	MHz
NF noise figure			-	1.9	-	dB
			-	3.1	-	dB

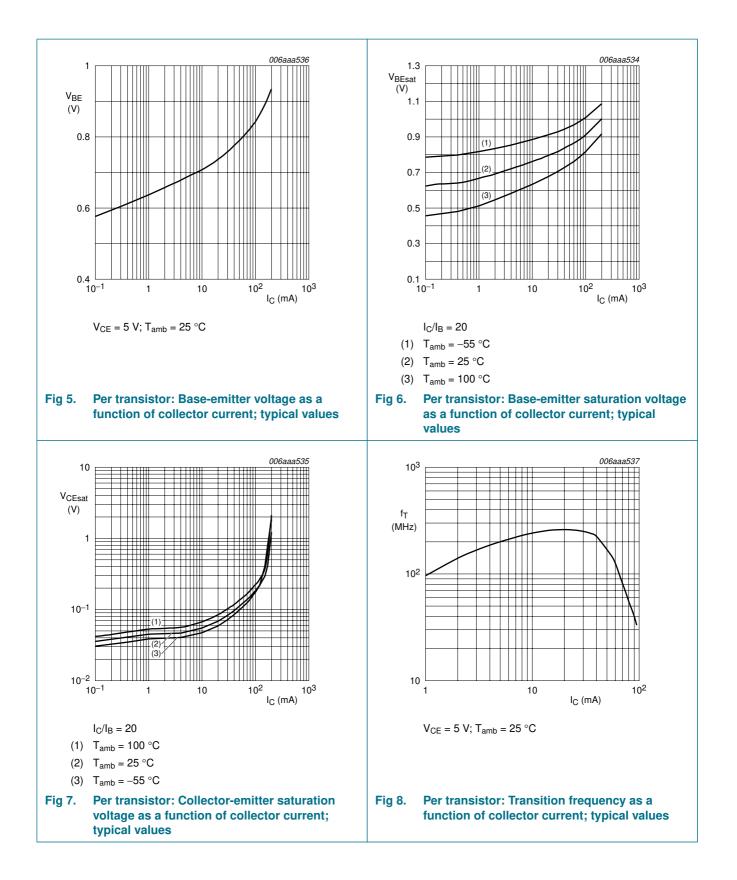
Table 8.Characteristics ...continued $T_{omb} = 25 \circ C$ unless otherwise specified



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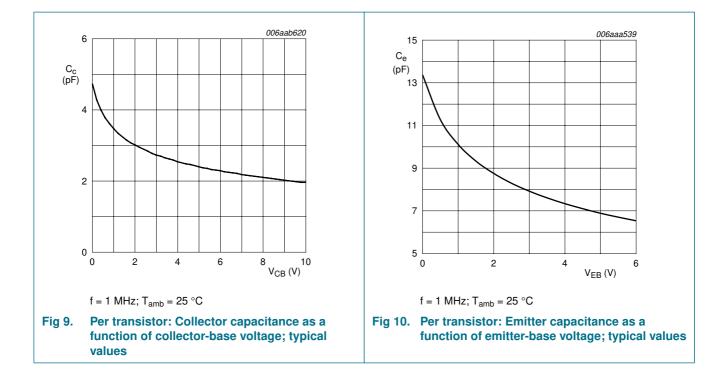
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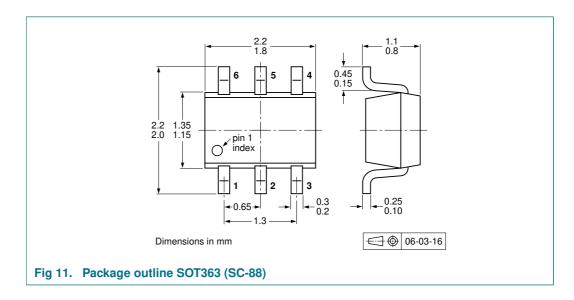
65 V, 100 mA NPN/NPN general-purpose transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
BC846BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	<u>[3]</u>	-125	-165

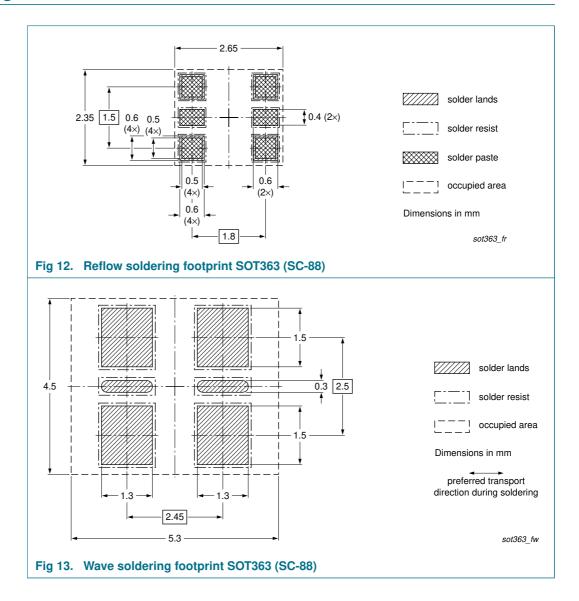
[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

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11. Soldering



BC846BS_1 Product data sheet

65 V, 100 mA NPN/NPN general-purpose transistor

12. Revision history

Table 10. Revision his	able 10. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
BC846BS_1	20090824	Product data sheet	-	-				

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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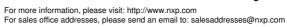
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